

**FEATURES**

High voltage transistor

MARKING: 2D



**MMBTA92 (PNP)**

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current -Continuous	I <sub>C</sub>	150	mA
Collector Power Dissipation	P <sub>C</sub>	0.4	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
Thermal Resistance, junction to Ambient	R <sub>JA</sub>	410	°C/mW



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-300		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-300		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CB</sub>	V <sub>CB</sub> =-200V, I <sub>E</sub> =0		-0.25	μA
Emitter cut-off current	I <sub>EB</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0		-0.1	μA
DC current gain	hFE(1)	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1mA	60		
	hFE(2)	V <sub>CE</sub> = -10V, I <sub>C</sub> =-10mA	100	200	
	hFE(3)	V <sub>CE</sub> = -10V, I <sub>C</sub> =-30mA	60		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-20mA, I <sub>B</sub> = -2mA		-0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -20mA, I <sub>B</sub> = -2mA		-0.9	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-20V, I <sub>C</sub> = -10mA f=30MHz	50		MHz

MMBTA92 Typical Characteristics

